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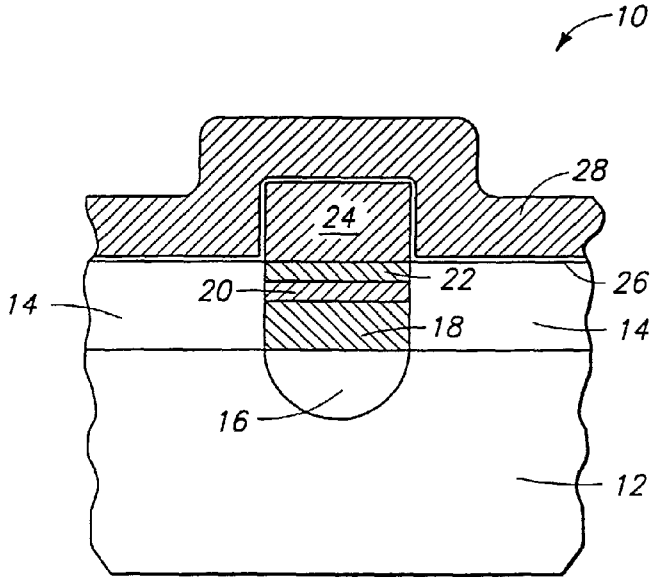
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(54) Title: METHODS OF FORMING METAL-COMPRISING MATERIALS AND CAPACITOR ELECTRODES; AND CAPACITOR CONSTRUCTIONS



(57) Abstract: The invention includes a method of forming a metal-comprising mass for a semiconductor construction. A semiconductor substrate is provided, and a metallo-organic precursor is provided proximate the substrate. The precursor is exposed to a reducing atmosphere to release metal from the precursor, and subsequently the released metal is deposited over the semiconductor substrate. The invention also includes capacitor constructions, and methods of forming capacitor constructions.

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